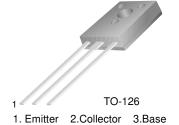


KSE700/701/702/703

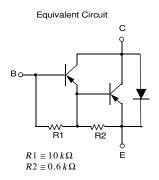
Monolithic Construction With Built-in Base-**Emitter Resistors**



PNP Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Sym- bol	Parameter	Value	Unit s
V _{CBO}	Collector- Base Voltage : KSE700/701	- 60	V
	: KSE702/703	- 80	V
V_{CEO}	Collector-Emitter Voltage: KSE700/701	- 60	V
	: KSE702/703	- 80	V
V _{EBO}	Emitter- Base Voltage	- 5	V
I _C	Collector Current	- 4	Α
I _B	Base Current	- 0.1	Α
P _C	Collector Dissipation (T _C =25°C)	40	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage : KSE700/701	I _C = - 10mA, I _B = 0	-60		V
	: KSE702/703		-80		V
I _{CEO}	Collector Cut-off Current : KSE700/701 : KSE702/703	$V_{CE} = -60V, I_{B} = 0$ $V_{CE} = -80V, I_{B} = 0$		-100 -100	μ Α μ Α
I _{CBO}	Collector Cut-off Current	V_{CB} = Rated BV_{CEO} , I_E = 0 V_{CB} = Rated BV_{CEO} , I_E = 0 $@T_C$ = 100°C		-100 -500	μA μA
I _{EBO}	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$		-2	mA
h _{FE}	DC Current Gain : KSE700/702 : KSE701/703	V _{CE} = - 3V, I _C = - 1.5A V _{CE} = - 3V, I _C = - 2A	750 750		
	: ALL DEVICES	$V_{CE} = -3V, I_{C} = -4A$	100		
V _{CE} (sat)	Collector-Emitter Saturation Voltage : KSE700/702 : KSE701/703 : ALL DEVICES	I _C = - 1.5A, I _B = - 30mA I _C = - 2A, I _B = - 40mA I _C = - 4A, I _B = - 40mA		-2.5 -2.8 -3	V V V
V _{BE} (on)	Base-Emitter On Voltage : KSE700/702 : KSE701/703	V _{CE} = - 3V, I _C = - 1.5A V _{CE} = - 3V, I _C = - 2A		-1.2 -2.5	V V
	: ALL DEVICES	V _{CE} = - 3V, I _C = - 4A		-3	V

Typical Characteristics

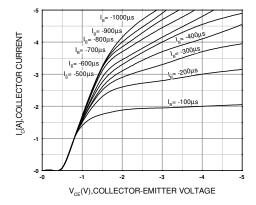


Figure 1. Static Characteristic

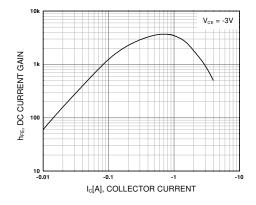


Figure 2. DC current Gain

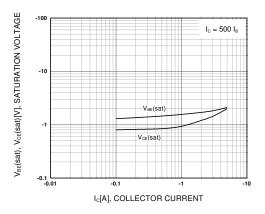


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

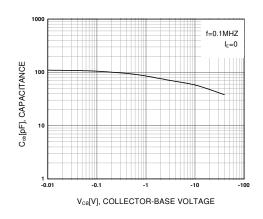


Figure 4. Collector Output Capacitance

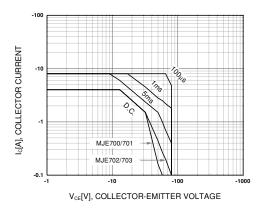


Figure 5. Safe Operating Area

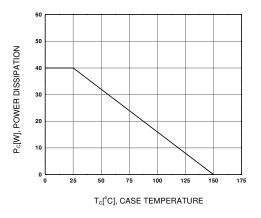
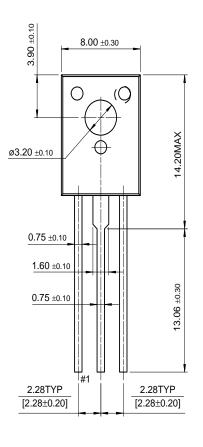


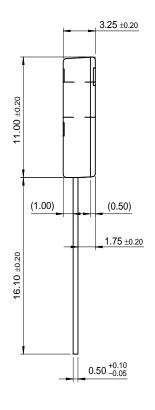
Figure 6. Power Derating

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Package Demensions

TO-126







Dimensions in Millimeters

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